
SEMICONDUCTOR

TECHNICAL DATA
DATA SHEET 516, REV. A

SILICON SCHOTTKY RECTIFIER DIE

Very Low Forward Voltage Drop

200°C Operating Temperature

Applications:

- Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging
- Out Performs 100 Volt Ultrafast Rectifiers

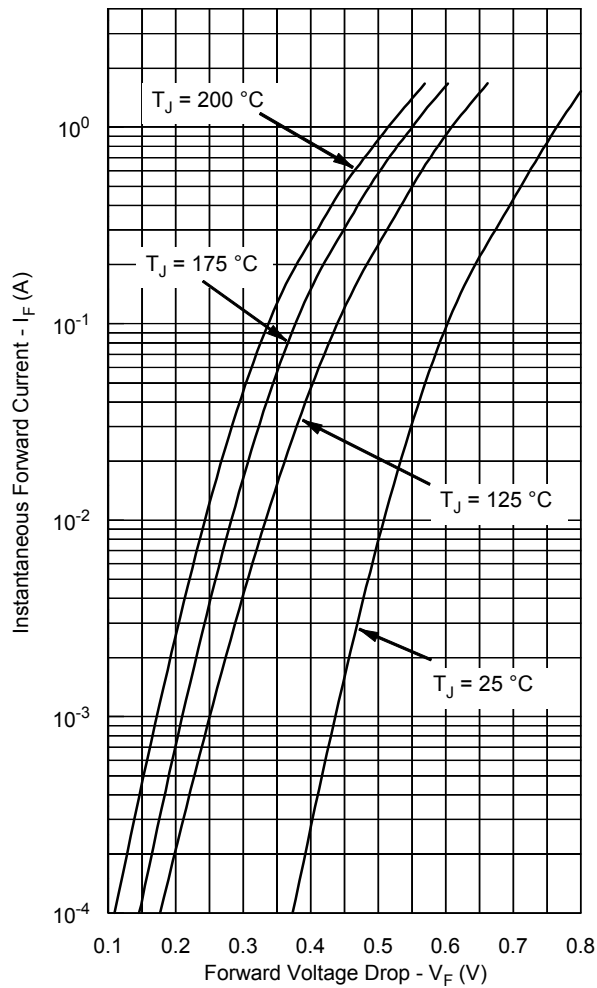
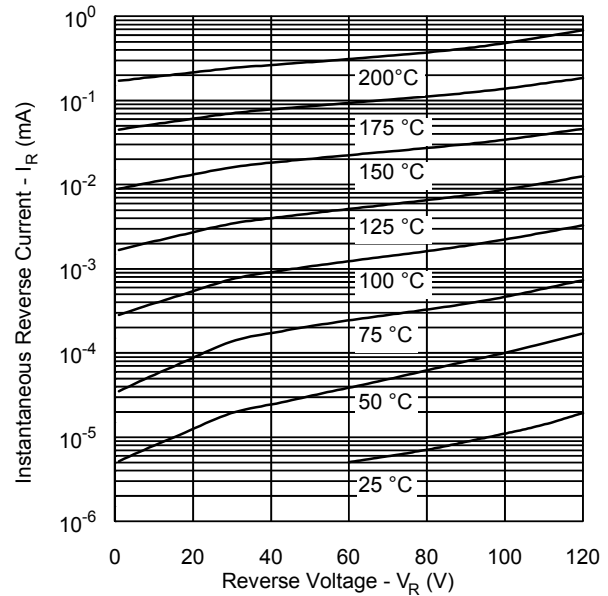
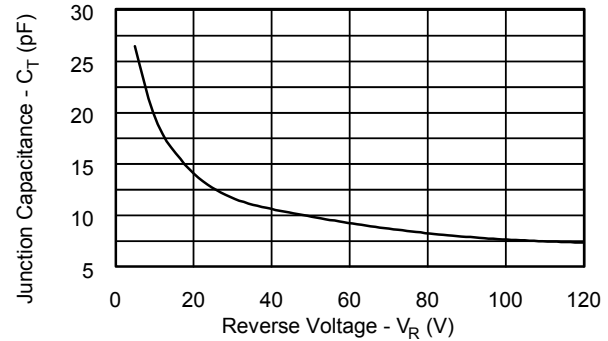
Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	1	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave ⁽¹⁾	20	A
Non-Repetitive Avalanche Energy	E_{AS}	$T_J = 25\text{ }^\circ\text{C}$, $I_{AS} = 0.13\text{ A}$, $L = 227\text{mH}$	2.0	mJ
Repetitive Avalanche Current	I_{AR}	I_{AS} decay linearly to 0 in $1\text{ }\mu\text{s}$ f limited by T_J max $V_A = 1.5V_R$	0.13	A
Max. Junction Temperature	T_J	-	-65 to +200	°C
Max. Storage Temperature	T_{stg}	-	-65 to +200	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 1A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.84	V
	V_{F2}	@ 1A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.68	V
Max. Reverse Current	I_{R1}	@ $V_R = 100\text{V}$, Pulse, $T_J = 25\text{ }^\circ\text{C}$	30	μA
	I_{R2}	@ $V_R = 100\text{V}$, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.6	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$, $V_{SIG} = 50\text{mV}$ (p-p)	35	pF

(1) in SHD package

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Typical Forward Characteristics

Typical Reverse Characteristics

Typical Junction Capacitance


SENSITRON

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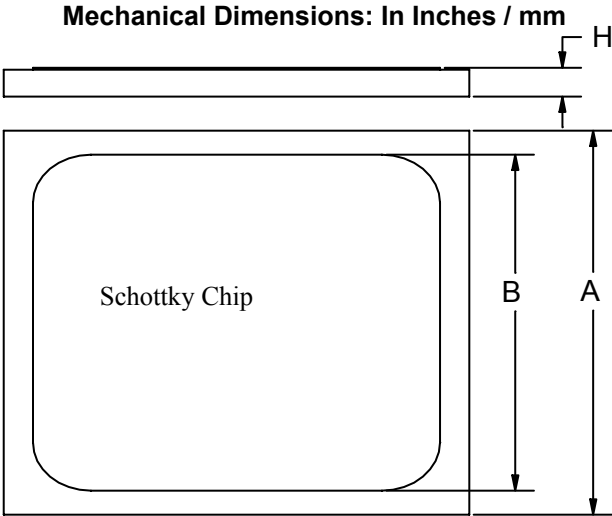


Figure 1

A	B	H
0.040±0.003	0.034±0.003	0.0105±0.001 (Al Top) 0.0155±0.001 (Ag Top)

Top side (Anode) metallization:
 A = Al - 25 kÅ minimum, Figure 1
 B = Ag - 30 kÅ minimum, Figure 1

Bottom side (Cathode) metallization:
 A, B = Ti/Ni/Ag - 30 kÅ minimum.

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